

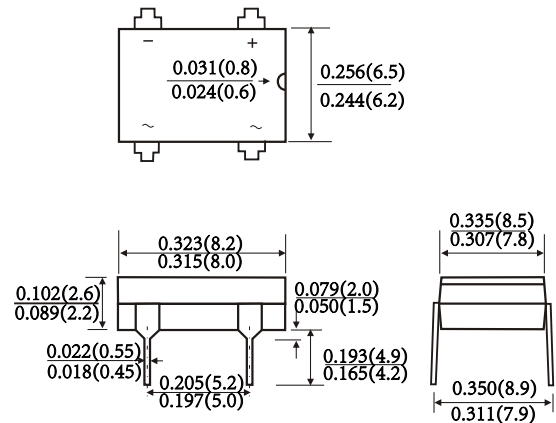
DB-1 SILICON BRIDGE RECTIFIER

FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- High reliability
- High temperature soldering guaranteed: 260 °C/10 seconds at terminals
- Component in accordance to RoHS 2015/863 and WEEE 2012/19/EU

MECHANICAL DATA

- Case style: DB-1 molded plastic
- Mounting position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

TYPE NUMBER		Symbols	DB151 DF I5005	DB152 DF I501	DB153 DF I502	DB154 DF I504	DB155 DF I506	DB156 DF I508	DB157 DF I510	Units
Maximum Recurrent Peak Reverse Voltage		VRRM	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage		VRMS	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage		VDC	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current		I(AV)	1.5							Amp
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		IFSM	50							Amps
Maximum Instantaneous Forward Voltage at 1K5 A DC		VF	1.1							Volts
Maximum DC Reverse Current at rated DC blocking voltage	TA=25 °C	IR	10							μA
	TA=125 °C		500							
Typical junction capacitance(Note 1)		CJ	25							pF
Typical thermal resistance(Note 2) Operating junction and storage temperature range		RθJA	40							K/W
		TJ TSTG	-55 to +150							°C

RATINGS AND CHARACTERISTIC CURVES

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

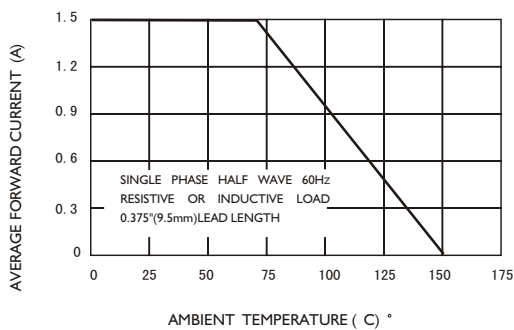


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

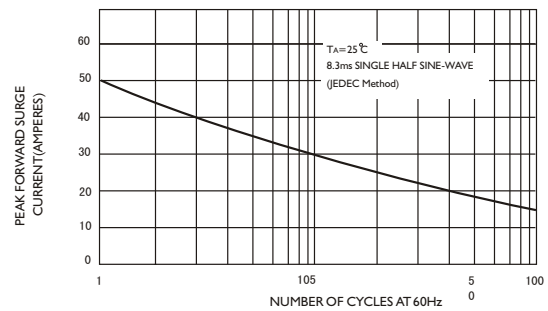


FIG.3-TYPICAL JUNCTION CAPACITANCE

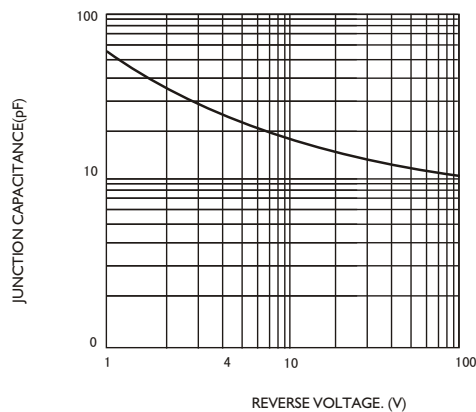


FIG.4-TYPICAL FORWARD CHARACTERISTICS

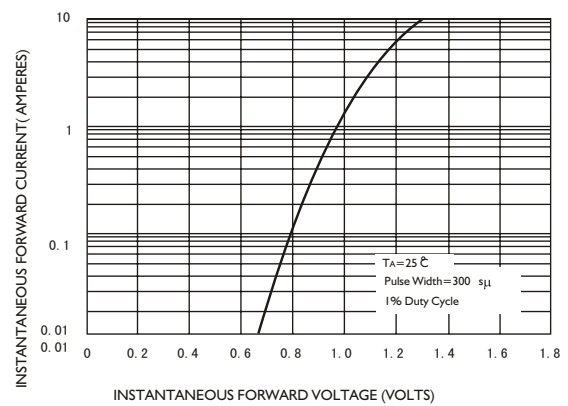


FIG.5-TYPICAL REVERSE CHARACTERISTICS

